SOT23-3 ṂṂ Ŀ P ێ MOS ʃ ᾧ̃ Ẕ ˥ S- CHANNEL MOSFET in a SOT23-3 Plastic Package.

ێ ʃ ᾧ̃ Ẕ ˥
Trench FET Power MOSFET.

ᴀ ᴅ Ȁ ʜ
High speed switch.

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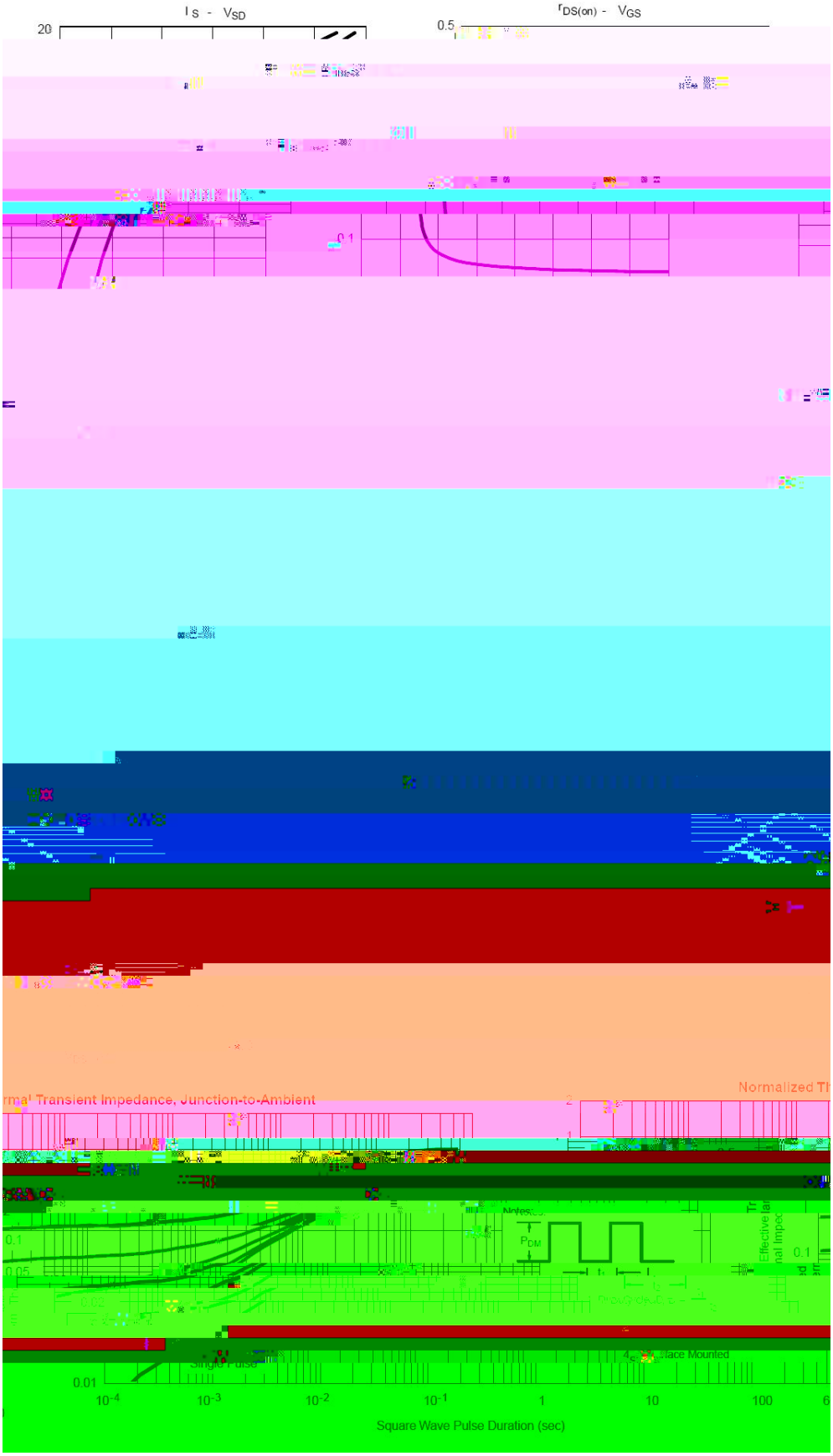
v ̈Ǫ	ϒ N	̈Ǫ Ö	D Ɉ
Parameter	Symbol	Rating	Unit

ƒ ÃÉ M ƒ

I D - VDS
I D - VGS
VDS (V)
VGS (V)
rDS(on) - ID
C - VDS
1200
900
0.30
0.25
0.20
Ciss
VGS = 1.8 V
VGS = 2.5 V
VGS = 4.5 V
Crss
0.10
300
0.00
ID (A)
VDS (V)
VGS - Qg
rDS(on) - TJ
VGS = 4.5 V
ID = 3.3 A
VDS = 10 V
ID = 3.3 A
TJ (°C)
Qg (nC)

⁝ ƎẶ́E ⅵ ƒ



I S - VSD
20
rDS(on) - VGS
0.5
0.1
rmal Transient Impedance, Junction-to-Ambient
Normalized Th
0.1
0.05
0.01
PDM
Single Pulse
Wave Mounted
10-4
10-3
10-2
10-1
1
10
100
Square Wave Pulse Duration (sec)

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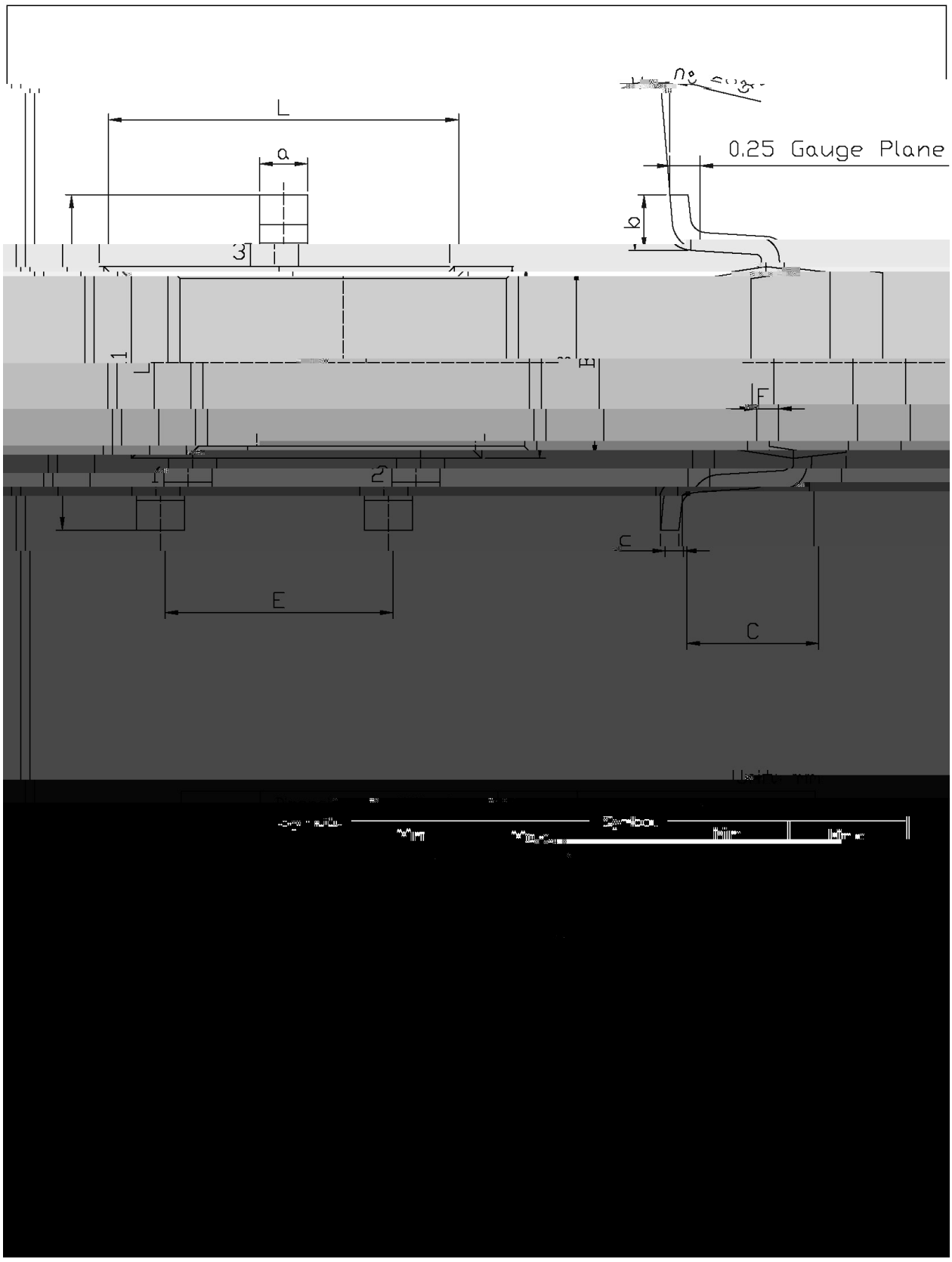

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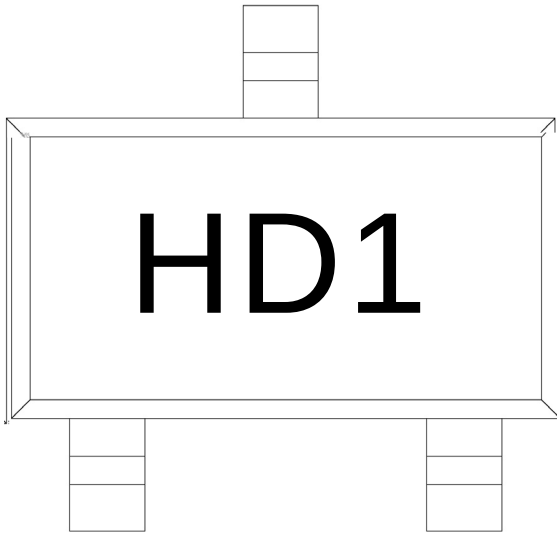

ب ˝ χ

H: ᵻ ɜ ᵎ Ґ

D1: ᵻ ʒ ᴺ Ґ

Note:

H: Company Code.

D1 χ Product Type

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